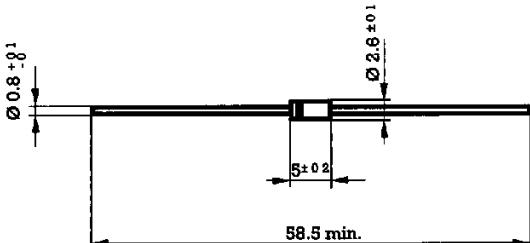


**1 Amp. Silicon Rectifier Diodes**

<b>Dimensions in mm.</b>  <b>Mounting instructions</b> <ol style="list-style-type: none"> <li>Min. distance from body to soldering point, 4 mm.</li> <li>Max. solder temperature, 350°C.</li> <li>Max. soldering time, 3,5 sec.</li> <li>Do not bend lead at a point closer than 2 mm. to the body.</li> </ol>	<b>DO-41 (Plastic)</b> <b>Voltage</b> 50 to 1.000 V. <b>Current</b> 1.0 A. at 75°C. <ul style="list-style-type: none"> <li>Low cost</li> <li>Diffused junction</li> <li>High current capability</li> <li>The plastic material carries U/L recognition 94 V-0</li> <li>Terminals: Axial Leads</li> <li>Polarity: Color band denotes cathode</li> </ul>
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**Maximum Ratings, according to IEC publication No. 134**

	1N 4001F	1N 4002F	1N 4003F	1N 4004F	1N 4005F	1N 4006F	1N 4007F	
$V_{RRM}$	Peak recurrent reverse voltage (V)	50	100	200	400	600	800	1000
$I_{F(AV)}$	Forward current at Tamb = 75°C				1 A			
$I_{FRM}$	Recurrent peak forward current				10 A			
$I_{FSM}$	8.3 ms. peak forward surge current (Jedec method)				30 A			
$T_j$	Max. operating temperature				175°C			
$T_{stg}$	Storage temperature range				– 65 to + 175°C			

**Electrical Characteristics at Tamb = 25°C**

$V_F$	Max. forward voltage drop at $I_F = 1 \text{ A}$	1.1V
$I_R$	Max. reverse current at $V_{RRM}$ at 25°C at 100°C	5 $\mu\text{A}$ 50 $\mu\text{A}$
$R_{thj-a}$	Max. thermal resistance ( $I = 10 \text{ mm.}$ )	50° C/W

## Characteristic Curves

FAGOR ELECTRONICS

